Abstract of the Disclosure

A circuit for driving a gate of a power metal-oxide semiconductor field effect transistor (MOSFET), which uses a higher voltage than a gate controller is provided. The circuit is able to safely and effectively transmits an output signal of a gate controller irrespective of a frequency and a duty-cycle of the output signal when transmitting the output signal of the gate controller to the power MOSFET using a higher voltage than the gate controller. Accordingly, the circuit is suitable for a case where the duty-cycle of the output signal of the gate controller dramatically changes and the frequency is irregular.